

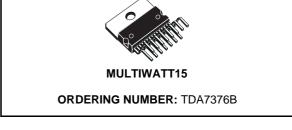
2 x 35W POWER AMPLIFIER FOR CAR RADIO

- HIGH OUTPUT POWER CAPABILITY: 2 x 40W max./4Ω
 2 x 35W/4Ω EIAJ
 2 x 25W4Ω @ 14.4V, 1KHz, 10%
 2 x 37W2Ω @ 14.4V, 1KHz, 10%
- 2Ω DRIVING
- DIFFERENTIAL INPUTS
- MINIMUM EXTERNAL COMPONENT COUNT
- INTERNALLY FIXED GAIN (26dB)
- MUTE FUNCTION (CMOS COMPATIBLE)
- AUTOMUTE AT MINIMUM SUPPLY VOLT-AGE DETECTION
- STAND-BY FUNCTION
- NO AUDIBLE POP DURING MUTE AND ST-BY OPERATIONS
- CLIPPING DETECTOR WITH PROGRAMMA-BLE DISTORTION THRESHOLD

PROTECTIONS:

- SHORT CIRCUIT (OUT TO GROUND, OUT TO SUPPLY VOLTAGE, ACROSS THE LOAD)
- OVERRATING CHIP TEMPERATURE WITH SOFT THERMAL LIMITER
- LOAD DUMP VOLTAGE
- FORTUITOUS OPEN GROUND
- LOUDSPEAKER DC CURRENT
- ESD

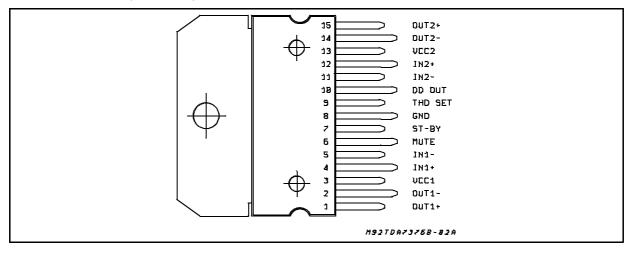
PIN CONNECTION (Continued)



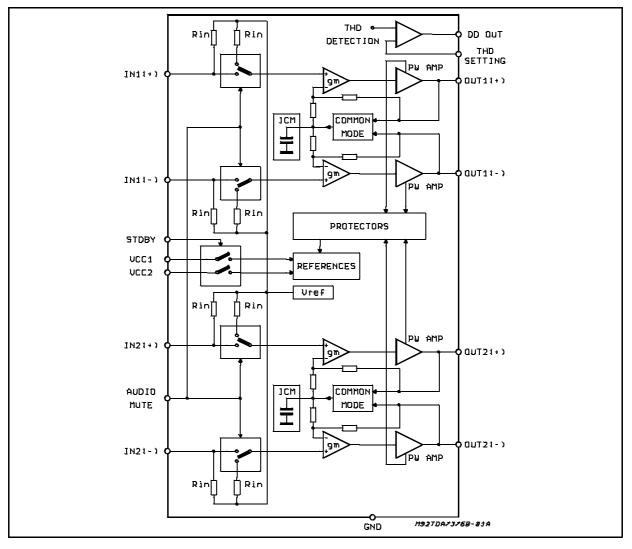
DESCRIPTION

The TDA7376B is a new technology dual bridge Audio Amplifier in Multiwatt 15 package designed for car radio applications. Thanks to the fully complementary PNP/NPN output stage configuration the TDA7376B delivers a rail-to-rail voltage swing with no need of bootstrap capacitors. Differential input pairs, that will accept either single ended or differential input signals, guarantee high noise immunity making the device suitable for both car radio and car boosters applications.

The audio mute control, that attenuates the output signal of the audio amplifiers, suppresses pop on - off transients and cuts any noises coming from previous stages. The St-By control, that debiases the amplifiers, reduces the cost of the power switch. The on-board programmable distortion detector allows compression facility whenever the amplifier is overdriven, so limiting the distortion at any levels inside the presettable range.



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{OP}	Operating Supply Voltage	18	V
Vs	DC Supply Voltage	28	V
V _{peak}	Peak Supply Voltage (t = 50ms)	50	V
Ι _Ο	Output Peak Current (non rep. t = 100µs) Output Peak Current (rep. f > 10Hz)	8 6	A A
P _{tot}	Power Dissipation at $T_{case} = 85^{\circ}C$	36	W
T _{stg,} T _j	Storage and Junction Temperature	-40 to 150	°C

THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th j-case}	Thermal Resistance Junction-case max.	1.8	°C/W

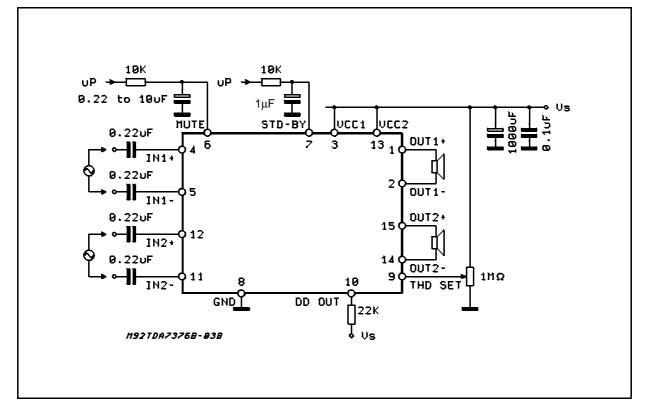
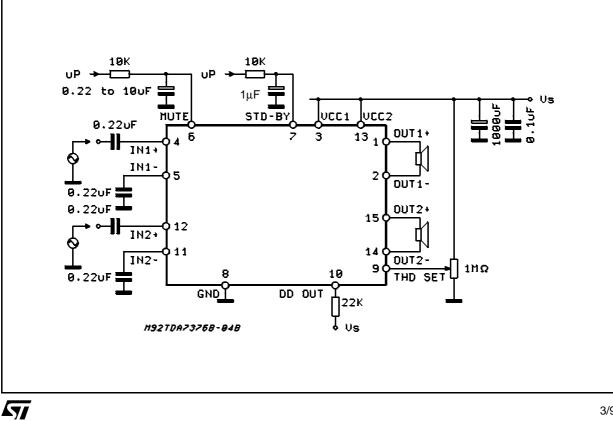


Figure 1: Differential Inputs Test and Application Circuit

Figure 2: Single Ended Inputs Test and Application Circuit



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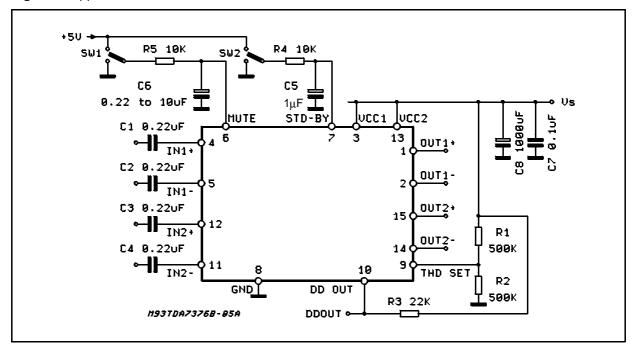
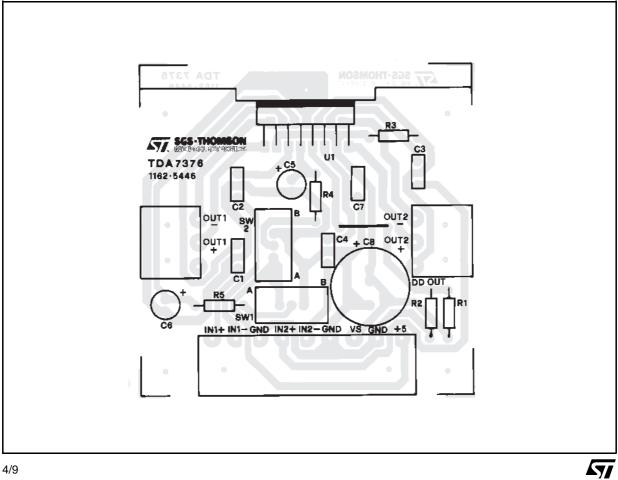


Figure 3: Application Board Reference Circuit

Figure 4: P.C. Board and Components Layout of the Circuit of Fig. 3 (1:1 scale)



Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		8		18	V
l _d	Total Quiescent Drain Current	R _L = ∞			200	mA
Vos	Output Offset Voltage				120	mV
Po	Output Power	THD = 10% THD = 10%, RL 2Ω	23 33	25 37		W W
P _{O max}	Max. Output Power (*)	VS = 14.4V	36	40		W
POEIAJ	EIAJ Output Power (*)	V _S = 13.7V	32	35		W
THD	Distortion	P _O = 0.5 to 10W P _O = 0.5 to 15W		0.03 0.08	0.3 0.5	% %
CT	Cross Talk	Talk f = 1KHz; Rg = 0 f = 10KHz; Rg = 0		80 70		dB dB
R _{IN}	Input Resistance	differential input single ended input	45 40			ΚΩ ΚΩ
G_V	Voltage Gain	Gain differential input 25 single ended input 25		26 26	27 27	dB dB
ΔG_V	Channel Gain Balance				1	dB
E _N	Input Noise Voltage	Rg = 600Ω ; "A Weighted" Rg = 600Ω ; 22Hz to 22KHz		3 4	6	μV μV
SVR	Supply Voltage Rejection	f = 100Hz; Vr = 1Vrms; Rg = 0 f = 10KHz; Vr = 1Vrms; Rg = 0	45	55		dB dB
BW	Power Bandwidth	(–3dB)	75			KHz
CMRR	Common Mode Rejection Ratio	ejection Ratio V _{CM} = 1Vrms input referred 6				dB
A _{SB}	Stand-by Attenuation	$V_{SB} = 1.5V$; $P_{Oref} = 1W$	80	90		dB
V _{sb IN}	Stand-by in Threshold				1.5	V
$V_{\text{sb}\text{OUT}}$	Stand-by out Threshold		3.5			V
I _{sb}	Stand-by Current Consumption				100	μΑ
AM	Mute Attenuation	V _M = 1.5V; P _{Oref} = 1W		85		dB
V _{MIN}	Mute in Threshold				1.5	V
V _{M OUT}	Mute out Threshold		3.5			V
l ₆	Mute pin Current	$V6 = 0$ to V_{S} ; $V_{S max.} = 18V$			100	μA
D_DL	Distortion Detection Level (**)		3.5			%
D _{DOUT}	Distortion Detector Output DC Current	Output low, sinked current (V _{pin10} = 1.5V)	1			mA
		Output high, leakage current (V _{pin10} = V _S , @ V _{Smax} = 18V)			10	μΑ

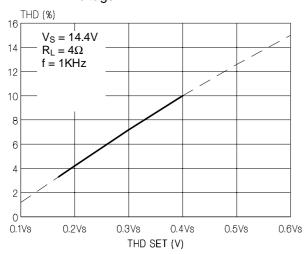
ELECTRICAL CHARACTERISTICS (Refer to the test fig. 1 and 2 circuit, $T_{amb} = 25^{\circ}C$; $V_S = 14.4V$; $f = 1 KHz; R_L = 4\Omega;$ unless otherwise specified.)

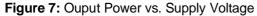
(*) Saturated square wave output (**) see figure 5 for THD setting.

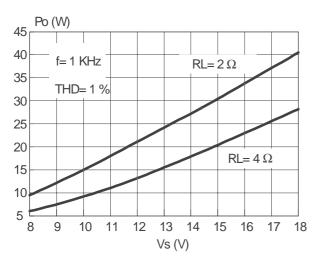
The TDA7376B is equipped with a programmable clipping distortion detector circuitry that allows to signal out the output stage saturation by providing a current sinking into an open collector output (DDout) when the total harmonic distortion of the output signal reaches the preset level. The desired threshold is fixed through an external divider that produces a proper voltage level across the THD set pin. Fig. 5 shows the THD detection threshold versus the THD set voltage. Since it is essential that the THD set voltage be proportional to the supply voltage, fig. 5 shows its value as a fraction of V_{CC}. The actual voltage can be computed by multiplying the fraction corresponding to the desired THD threshold by the application's supply voltage.

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Figure 5: Clip Detector Threshold vs. THD set. Voltage.









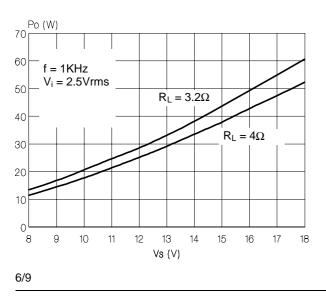


Figure 6: Quiescent Current vs. Supply Voltage

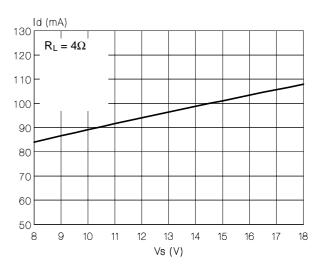
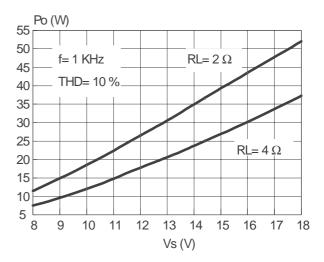
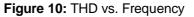
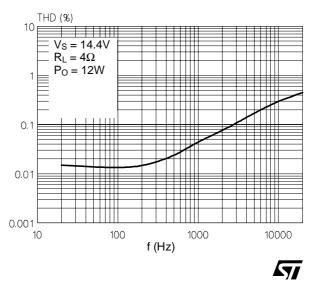


Figure 8: Ouput Power vs. Supply Voltage







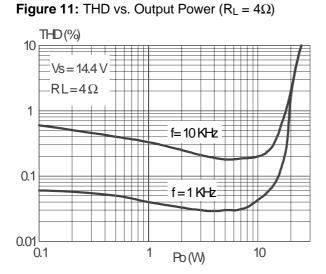
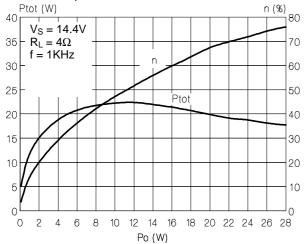


Figure 13: Dissipated Power & Efficiency vs. Output Power





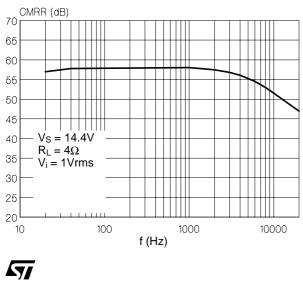


Figure 12: THD vs. Output Power ($R_L = 24\Omega$)

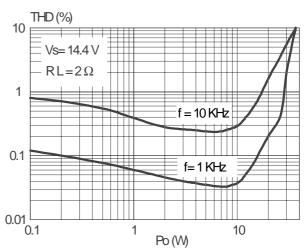
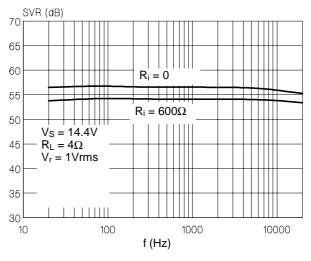
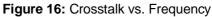
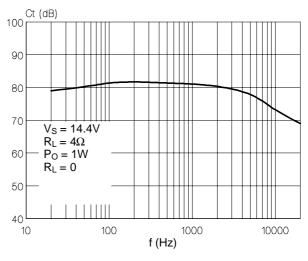


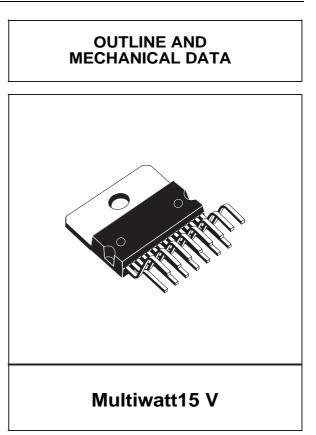
Figure 14: SVR vs. Frequency

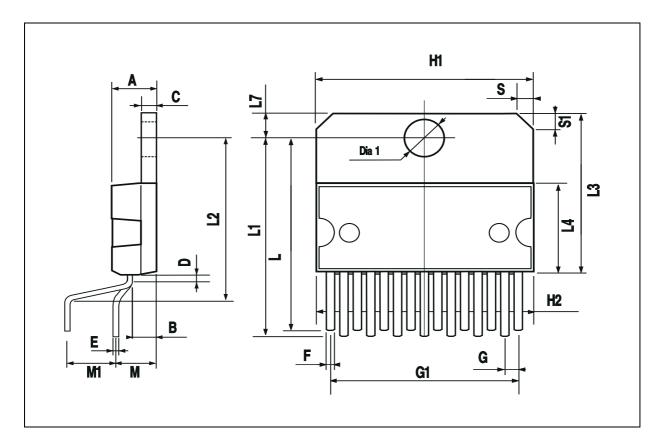






DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			5			0.197	
В			2.65			0.104	
С			1.6			0.063	
D		1			0.039		
Е	0.49		0.55	0.019		0.022	
F	0.66		0.75	0.026		0.030	
G	1.02	1.27	1.52	0.040	0.050	0.060	
G1	17.53	17.78	18.03	0.690	0.700	0.710	
H1	19.6			0.772			
H2			20.2			0.795	
L	21.9	22.2	22.5	0.862	0.874	0.886	
L1	21.7	22.1	22.5	0.854	0.870	0.886	
L2	17.65		18.1	0.695		0.713	
L3	17.25	17.5	17.75	0.679	0.689	0.699	
L4	10.3	10.7	10.9	0.406	0.421	0.429	
L7	2.65		2.9	0.104		0.114	
М	4.25	4.55	4.85	0.167	0.179	0.191	
M1	4.63	5.08	5.53	0.182	0.200	0.218	
S	1.9		2.6	0.075		0.102	
S1	1.9		2.6	0.075		0.102	
Dia1	3.65		3.85	0.144		0.152	





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